

forming on a surface an intrinsic or substantially intrinsic semiconductor film having [an intrinsic or substantially intrinsic] a region to become a channel region of the transistor, said semiconductor film containing therein carbon, nitrogen or oxygen at a concentration of 1×10^{19} atoms/cm³ or less, said semiconductor film comprising a material selected from the group consisting of germanium and a germanium silicon alloy; and irradiating said entire semiconductor film with a laser beam or a light having a strength equivalent to the laser beam with melting the semiconductor film to increase the degree of crystallinity thereof.

36. (Twice Amended) A thin film transistor produced by a process comprising the steps of:

forming on a surface an intrinsic or substantially intrinsic semiconductor film having [an intrinsic or substantially intrinsic] a region to become a channel region of the transistor, said semiconductor film containing therein carbon at a concentration of 1×10^{19} atoms/cm³ or less, said semiconductor film comprising a material selected from the group consisting of germanium and a germanium silicon alloy; and

irradiating the semiconductor film with a laser beam or a light having a strength equivalent to the laser beam to increase the degree of crystallinity of the semiconductor film.

37. (Twice Amended) A thin film transistor produced by a process comprising the steps of:

forming on a surface an intrinsic or substantially intrinsic semiconductor film having [an intrinsic or substantially intrinsic] a region to become a channel region of the transistor, said semiconductor film containing therein nitrogen at a concentration of 1×10^{19} atoms/cm³ or less,